

Study of the ionization efficiency for nuclear recoils

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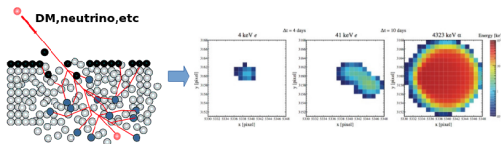
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Introduction

- In experiments for direct dark matter searches or detection of (CEN ν S), the experimental signal entails the detection of the ionization produced by the recoiling target ions following a scattering event.



- The electronic excitation produced by a recoiling ion is typically smaller than that produced by an electron of the same energy, we name this as **quenching** ($[eV_{nr}] \rightarrow [eV_{ee}]$).

$$quenching = \frac{\text{total ionization energy}}{\text{total deposited energy}} = f_n = \frac{\bar{\eta}}{\varepsilon_R}$$

where $\bar{\eta}$ and ε_R are the ionization energy and the total recoil energy in adimensional units.

Introduction

- In 1963, Lindhard gave a parametrization for the quenching, but it is only acceptable for energy depositions ($\gtrsim 10$ keV).
- Recent measurements of the QF for nuclear recoils in silicon (Si) reveal a clear deviation from Lindhard formula, below $E_R < 4$ keV.
- Lindhard neglected the binding energy term. He end with a simplified integro-differential equation.
- In this work we incorporate correctly the binding energy term into the physical basic equation.
- This leads to a modify integro-differential equation that can be solved numerically.

Importance of Quenching Factor for DM and ν experiments.

Remark

Different quenching, e.g Lindhard and Chavarria, change significantly the rate for recent CONNIE results (*PhysRevD.100.092005*).

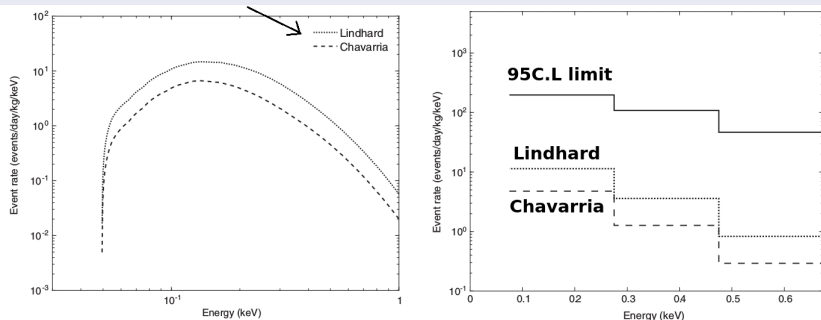


Figure: (left) Observable neutrino recoil spectrum in the CONNIE, (right) CE ν NS event rate: 95% confidence level limit from the reactor on-off

Importance of Quenching Factor for DM and ν experiments.

For DM searches with pure crystals the quenching play an important role for calibration and efficiency.

The cutoff for the efficiency is about $60 \text{ eV}_{\text{ee}}$ that correspond to $\sim (0.3 \pm 0.1) \text{ keV}_{\text{nr}}$.

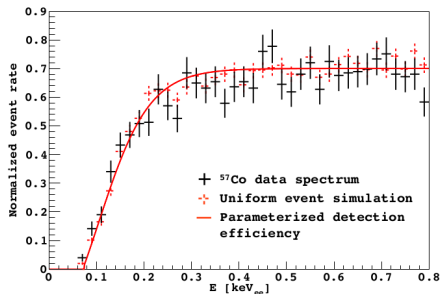


Figure: Detection efficiency, used for the WIMP search analysis (*Phys. Rev. D* 94, 082006).

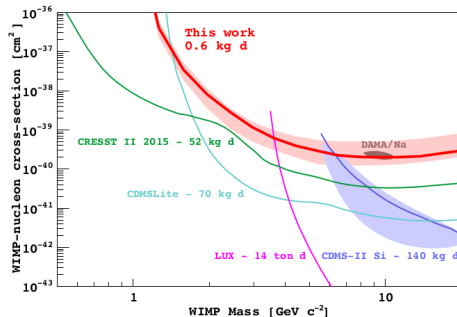
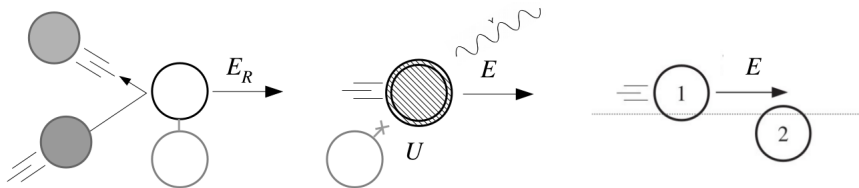


Figure: DAMIC 0.6 kg limit.

The model

- Consider an ion in a homogeneous substance moving with a kinetic energy E , after recoiling off an interaction with an incident particle (e.g., a DM particle).
- Suppose that the ion recoils from the interaction with an energy E_R , and that an energy U is lost to some disruption of the atomic bonding, then $E_R = E + U$
- The moving ion sets off a cascade of slowing-down processes that dissipate the energy E throughout the medium.



The model

Lindhard considered the atomic movement $\bar{\nu}$ an additive quantity over the individual slowing-down processes generated by the initial scattering, for $\bar{\nu}$ the equation is

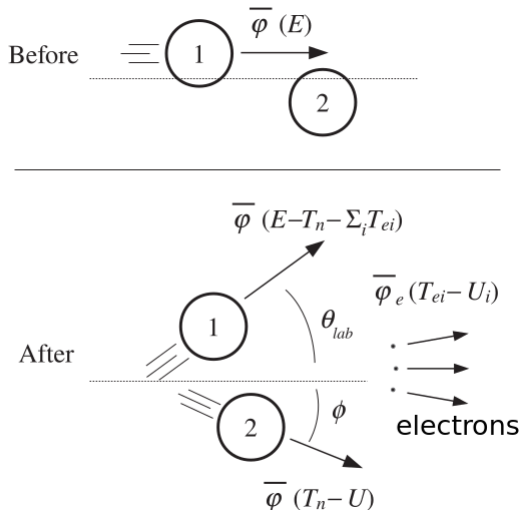
$$\int d\sigma_{n,e} [\bar{\nu}(E - T_n - \sum_i T_{ei}) + \bar{\nu}(T_n - U) - \bar{\nu}(E) + \sum_i \bar{\nu}_e(T_{ei} - U_{ei})] = 0 \quad (1)$$

where T_n and T_{ei} are the energies transferred to nuclei and electrons in the CM frame.

Lindhard originally neglects the binding energy in all his computations.

The model

Here $\bar{\phi} = \bar{\nu}$, can be any additive physical quantity.



The model

In order to compute a solution for $\bar{\nu}$, we have to make five approximations.

- i Neglect atomic movement from electrons, since it is negligible at low energies $\bar{\nu}_e = 0$.
- ii Energy transferred to ionized electrons is small compared to that transferred to recoiling ions.
- iii Effects of electronic and atomic collisions can be treated separately; $\varepsilon_R = \bar{\eta} + \bar{\nu}$.
- iv T_n is also small compared to the energy E .
- v Expand the terms in Eq. 1 up to **second order including binding energy**.

Simplified integral equation with binding energy

With the above remarks and with the use of the electronic stopping power $S_e = k\varepsilon^{1/2}$ (with k a constant) and the nuclear stopping $d\sigma_n(t)$ with $t = \varepsilon^2 \sin^2(\theta/2)$, we can transform Eq.1 to:

$$-\frac{1}{2}k\varepsilon^{3/2}\bar{v}''(\varepsilon) + \underbrace{k\varepsilon^{1/2}}_{S_e}\bar{v}'(\varepsilon) = \int_{\varepsilon u}^{\varepsilon^2} \underbrace{dt \frac{f(t^{1/2})}{2t^{3/2}}}_{d\sigma_n} [\bar{v}(\varepsilon - t/\varepsilon) + \bar{v}(t/\varepsilon - u) - \bar{v}(\varepsilon)] \quad (2)$$

This equation can be solved numerically from $\varepsilon \geq u$. So the equation predicts a threshold energy of u ($\varepsilon_R^{threshold} = 2u$). The function $f(t)$ is related to the interatomic potential (e.g Thomas-Fermi).

The equation admits a solution featuring a "kink" at $\varepsilon = u$ (discontinuous 1st derivative).

Numerical solution

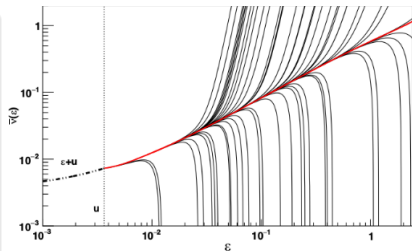
Shooting method

We have the boundary condition $\bar{v}''(\varepsilon \rightarrow \infty) \rightarrow 0$.

Now, since the R.H.S of Eq. 2 is zero at $\varepsilon = u$ and lower, we impose that the L.H.S to be zero at this point, this gives the relation

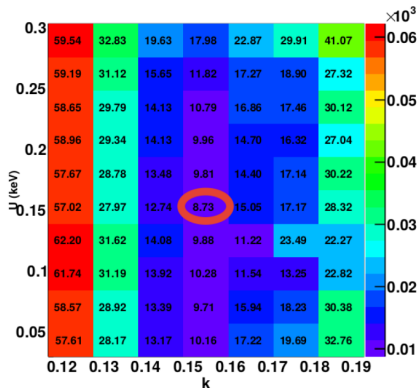
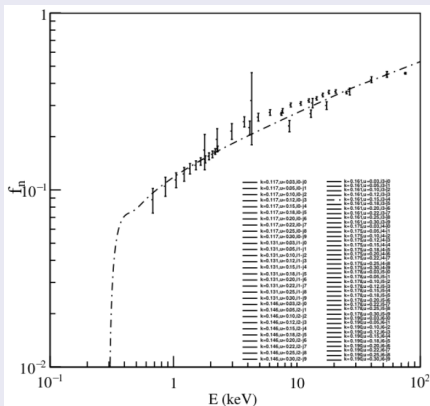
$$\bar{v}'(u) = \frac{u}{2} \bar{v}''(u)$$

So we give an initial try of \bar{v}' to get the boundary condition, we shoot in this way until the boundary condition is satisfy.



Fits to data

We set a grid of 7×7 points in U and k region, in an acceptable ranges, and compute the χ^2/ndf of each (U, k) point to determine the optimal value, we do this for Si and Ge.



Fits to data

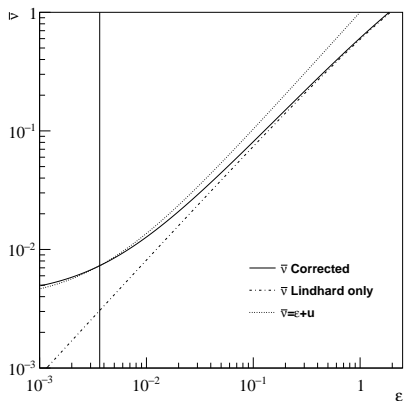
In general, U includes both the energy needed to remove the ion from its site and contributions to excitation of bound atomic electrons, therefore incorporates the Migdal effect.

Silicon*			Germanium*			
Shell	$U(\text{eV})$	$\#e$	Shell	$U(\text{eV})$	$\#e$	
$[\text{Ne}]^4$		4	$[\text{Ar}]^{18}$		18	
$2p$	100	6	$3d$	30	10	(3)
Average $e - h$	3.7	4	Average $e - h$	3.0	4	
Dislocation	36		Dislocation	23		

* E. Clementi and D.L.Raimondi, J. Chem. Phys. 1963, 38, 2686.

Ansatz

- We can implement a good analytical approximation to solve the integral equation.
- The idea is to lessen the ionization contribution, subtracting a fraction of the electronic stopping power.
- $\bar{\eta} = \bar{\eta}_{lind} - c\varepsilon^{1/2} - c'$ where c , c' and u are estimated from a fit to the available data.
- Where $\bar{\eta} = \varepsilon - \bar{\nu}$.



Results (Error band approximate cover the data fluctuation)

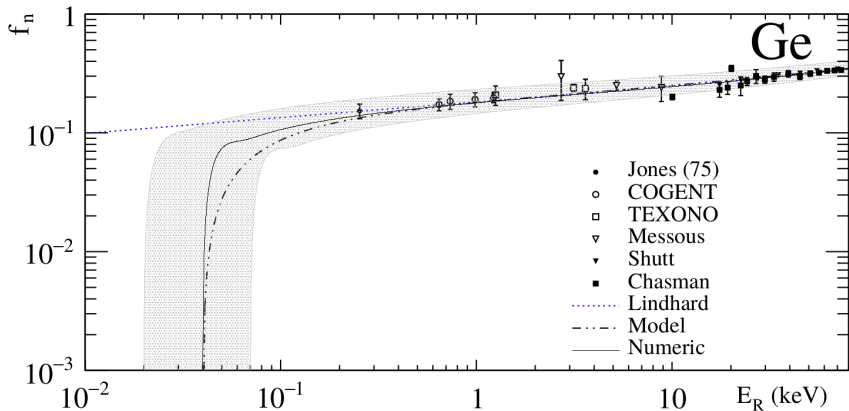


Figure: Measurements of the QF in Ge (points with error bars) compared to the Lindhard model (dot-dashed line), the fitted ansatz, and the numerical solution with $U = 0.02$ keV and $k = 0.162$.

Results

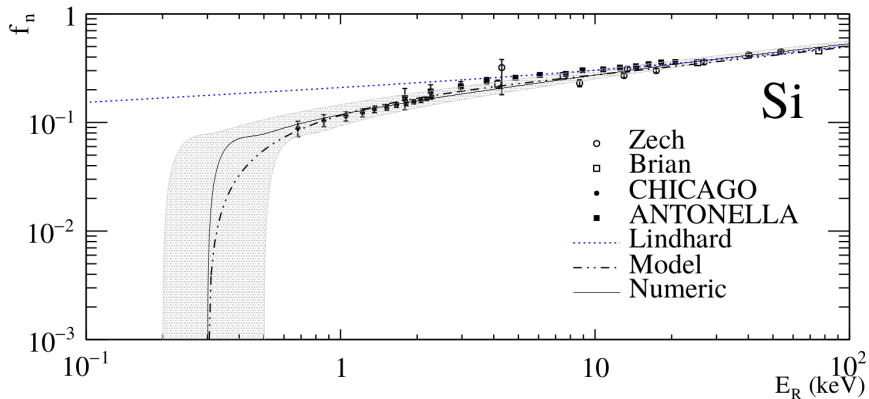


Figure: Measurements of the QF in Si (points with error bars) compared to the Lindhard model (dot-dashed line), the fitted ansatz, and the numerical solution with $U = 0.15$ keV and $k = 0.161$.

Conclusions

- 1 We found an appropriate form for the basic integro-differential equation describing the energy given to atomic motion by nuclear recoils in pure crystals, when a constant binding energy is considered.
- 2 Measurements of QF in Ge detectors are well described by our model.
- 3 In the case of Si, the QF measurements are well described by our model if the binding energy is in the range 100-250 eV, where this is consistent with DAMIC data estimate (cutoff of ≈ 0.3 keV).
- 4 The predicted cutoff for Si is much larger than the Frenkel (dislocation) energy of about 36 eV, and therefore also greater than the physical cutoff.
- 5 This model can be extended considering energy variable binding energy and modify expression for S_e for low energies. Work in progress.